



SOT-323 Plastic-Encapsulate Transistors

MMST4403 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.2 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.6 A

Collector-base voltage

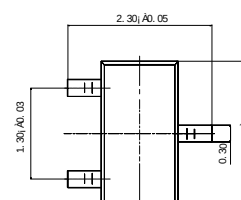
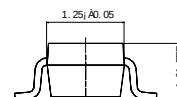
$V_{(BR)CBO}$: -40 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-323

1. BASE
2. EMITTER
3. COLLECTOR



Unit: mm

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-35V, I_E=0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-35V, I_B=0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$		-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-2V, I_C=-150mA$	100	300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-150mA, I_B=-15mA$		-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-150mA, I_B=-15mA$		-0.95	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-20mA$ $f=100MHz$	200		MHz
Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0$ $f=1MHz$		8.5	pF
Delay time	t_d	$V_{CC}=-30V, I_C=-150mA$		15	nS
Rise time	t_r	$V_{BE(off)}=-2V, I_{B1}=-15mA$		20	nS
Storage time	t_s	$V_{CC}=-30V, I_C=-150mA$		225	nS
Fall time	t_f	$I_{B1}=I_{B2}=-15mA$		30	nS

Marking

:K3T